



74LVCH244A

OCTAL BUFFER/LINE DRIVER WITH BUS HOLD / 3 STATE OUTPUTS

# Description

The 74LVCH244A provides two 4-bit line drivers with separate output-enable  $\overline{(OE)}$  inputs. When  $\overline{OE}$  is low, the device passes data from the A inputs to the Y outputs. When OE is high, the outputs are in the high-impedance state.

The device is designed for operation with a power supply range of 1.65V to 3.6V.

The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

Bus hold circuitry holds unused or un-driven inputs at a high or low logic state. The use of external pull-up or pull down resistors is not recommended.

### Features

- Supply Voltage Range from 1.65V to 3.6V
- Sinks or Sources 24mA at V<sub>CC</sub> = 3V
- CMOS Low Power Consumption
- IOFF Supports Partial-Power Down Operation
- Inputs or Outputs Accept up to 5.5V
- Inputs Can be Driven by 3.3V or 5V Allowing for Mixed Voltage Applications
- Schmitt Trigger Action at All Inputs
- Typical V<sub>OLP</sub> (Quiet Output Ground Bounce) less than 0.8V with V<sub>CC</sub> = 3.3V and T<sub>A</sub> = +25°C
- Typical V<sub>OHV</sub> (Quiet Output Dynamic VOH) greater than 2.0V with V<sub>CC</sub> = 3.3V and T<sub>A</sub> =  $+25^{\circ}$ C
- ESD Protection Tested per JESD 22
- Exceeds 200-V Machine Model (A115)
- Exceeds 2000-V Human Body Model (A114)
- Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 250mA per JESD 78, Class I
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. Green" Device (Note 3)

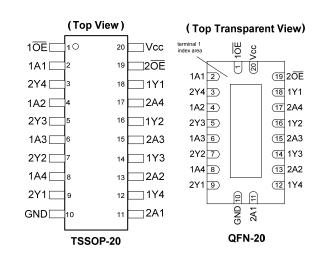
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

#### **Pin Assignments**

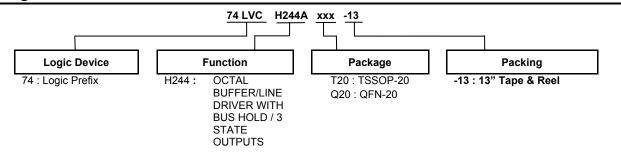


## Applications

- General Purpose Logic
- Bus Driving
- Power Down Signal Isolation
- Wide array of products such as:
  - PCs, Notebooks, Netbooks, Ultrabooks
  - Networking Computer Peripherals, Hard Drives, CD/DVD ROM
  - TV, DVD, DVR, set top box



## **Ordering Information**



Part Number	Package	Package	Package	13" Таре	and Reel
Part Nulliber	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74LVCH244AT20-13	T20	TSSOP-20	6.4mm X 6.5mm X 1.2mm 0.65 mm lead pitch	2500/Tape & Reel	-13
74LVCH244AQ20-13	Q20	V-QFN4525-20	2.5mm X 4.5mm X 0.95mm 0.50 mm lead pitch	2500/Tape & Reel	-13

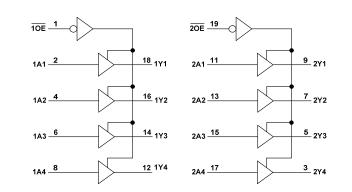
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. V-QFN4525-20 is a JEDEC recognized naming convention that specifies the package thickness category as V and the number 4525 describes the package as 4.5mm X 2.5mm.

# **Pin Descriptions**

Pin Number	Pin Name	Description
1	10E	Output Enable 1
2	1A1	Data Input
3	2Y4	Data Output
4	1A2	Data Input
5	2Y3	Data Output
6	1A3	Data Input
7	2Y2	Data Output
8	1A4	Data Input
9	2Y1	Data Output
10	GND	Ground
11	2A1	Data Input
12	1Y4	Data Output
13	2A2	Data Input
14	1Y3	Data Output
15	2A3	Data Input
16	1Y2	Data Output
17	2A4	Data Input
18	1Y1	Data Output
19	20E	Output Enable 2
20	V <sub>CC</sub>	Supply Voltage

# Logic Diagram



### **Function Table**

(Each 4-Bit Buffer)					
INPU	OUTPUT				
OE	Α	Y			
L	Н	Н			
L	L	L			
Н	Х	Z			



## Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to +7.0	V
VI	Input Voltage Range	-0.5 to +7.0	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0V	-20	mA
I <sub>OK</sub>	Output Clamp Current V <sub>O</sub> < 0V	-50	mA
lo	Continuous Output Current -0.5V < V <sub>O</sub> V <sub>CC</sub> +0.5V	±50	mA
Icc	Continuous Current Through V <sub>CC</sub>	100	mA
I <sub>GND</sub> Continuous Current Through GND		-100	mA
T <sub>J</sub> Operating Junction Temperature		-40 to +150	°C
T <sub>STG</sub> Storage Temperature		-65 to +150	°C
Ртот	Total Power Dissipation	500	mW

Notes:

NEW PRODUCT

6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

# **Recommended Operating Conditions**

Symbol	Parameter	Conditions	Min	Max	Unit	
V <sub>a</sub>	Supply Voltage	Operating	1.65	3.6	V	
V <sub>CC</sub>	Supply voltage	Data Retention Only	1.5	—	V	
VI	Input Voltage	—	0	5.5	V	
Vo	Output Voltage	—	0	Vcc	V	
		V <sub>CC</sub> = 1.65V	—	-4		
	High-Level Output Current	V <sub>CC</sub> = 2.3V	—	-8	mA	
I <sub>OH</sub>		V <sub>CC</sub> = 2.7V	—	-12	ША	
		V <sub>CC</sub> = 3.0V	—	-24		
		V <sub>CC</sub> = 1.65V	—	4		
	Low Lovel Output Current	V <sub>CC</sub> = 2.3V	—	8	mA	
I <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 2.7V	—	12	ША	
		V <sub>CC</sub> = 3.0V	—	24		
Δt/ΔV	Input Transition Rise or Fall Rate		—	10	ns/V	
T <sub>A</sub>	Operating Free-Air Temperature		-40	+125	°C	



# **Electrical Characteristics**

Symbol	Parameter	Test Conditions	V.	T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit
			1.65V to 1.95V	V <sub>CC</sub> X 0.65	_	V <sub>CC</sub> X 0.65	—	
V <sub>IH</sub> High-Level Input Voltage		2.3V to 2.7V	1.7		1.7	_	V	
	Voltage		3.0V to 3.6V	2	—	2	_	
			1.65V to 1.95V	—	V <sub>CC</sub> X 0.35	—	V <sub>CC</sub> X 0.35	
VIL	Low-Level input voltage		2.3V to 2.7V	—	0.7	—	0.7	V
	· ondgo		3.0V to 3.6V	—	0.8	_	0.8	
		I <sub>OH</sub> = -5μA	1.65V to 5.5V	V <sub>CC</sub> -0.2	—	V <sub>CC</sub> -0.3	—	
		I <sub>OH</sub> = -4mA	1.65V	1.2	—	1.05	—	
V	High-Level	I <sub>OH</sub> = -8mA	2.3 V	1.7	_	1.65	—	
V <sub>OH</sub>	Output Voltage	L = 10mA	2.7V	2.2	_	2.05	_	V
		I <sub>OH</sub> = -12mA	3.0V	2.4	—	2.48	—	V
		I <sub>OH</sub> = -24mA	3.0V	2.3	—	2.0	—	
		I <sub>OL</sub> = 100μA	1.65V to 5.5V	—	0.2	—	0.3	
		I <sub>OL</sub> = 4mA	1.65V	_	0.45		0.65	
V <sub>OL</sub>	Low-Level Output Voltage	I <sub>OL</sub> = 8mA	2.3V	_	0.60	_	0.80	V
voltage	vollage	I <sub>OL</sub> = 12mA	2.7V	—	0.40	—	0.60	
		I <sub>OL</sub> = 24mA	3.0V	—	0.55	_	0.80	
I <sub>OFF</sub>	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 0 or 5.5V	0	_	±10	_	20	μΑ
l <sub>l</sub>	Input Current Control Pins	V <sub>I</sub> = GND or 5.5V	0 to 5.5V	_	±5	—	± 20	μΑ
		VI = 0.58V		25	—	15	—	
		V <sub>I</sub> = 1.07	1.65V	-25	—	-15	—	
	Input Current	V <sub>1</sub> = 0.7V	0.01 <i>/</i>	45		35	_	
I <sub>I(HOLD)</sub>	Required to	V <sub>I</sub> = 1.7V	2.3V	-45		-35	_	μA
	Change State	V <sub>I</sub> = 0.8V		75	—	60	—	
		V <sub>1</sub> = 2.0V	3.0V	-75	—	-60	—	
		V <sub>I</sub> = 0 or 3.6V	3.6V		±500		±500	
I <sub>OZ</sub>	Z-State Current	V <sub>1</sub> =GND or 5.5V V <sub>O</sub> = 0 or 5.5V	3.6V	_	±5	_	± 20	uA
I <sub>CC</sub>	Supply Current	$V_{I} = GND \text{ or}$ $V_{CC, I_{O}} = 0$	6.0V	_	10	_	40	μΑ
$\Delta I_{CC}$	Additional Supply Current	One input at $V_{CC} - 0.6V I_O = 0A$	2.7V to 3.6V	_	500	_	5000	μΑ
Ci	Input Capacitance	VI = GND or V <sub>CC</sub>	3.3V	4.0 ty	/pical	4.0 ty	/pical	- 5
Co	Output Capacitance	$V_0$ = GND or $V_{CC}$	3.3V	5.5 ty	/pical	5.5 ty	/pical	pF



# **Switching Characteristics**

Symbol	Parameter	Test Conditions	Vcc	т	<sub>A</sub> = +25°	°C	T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
			1.8V ± 0.15V	1	5.9	12	1	12.2	1	12.4	
	Propagation	Figure 1	2.5V ± 0.2V	1	4.2	7.8	1	8.4	1	10	
t <sub>PD</sub>	Delay $A_N$ to $Y_N$	-	2.7V	1	4.2	8.2	1	8.9	1	9	ns
			3.3V ± 0.3V	1.5	3.9	7.7	1.5	8.2	1.5	8.3	
		1.8V ± 0.15V	1	6.4	12.1	1	12.6	1	14.1		
4	Enable Time	i iguic i	2.5V ± 0.2V	1	4.6	9.1	1	9.6	1	11.7	
t <sub>EN</sub>	$\overline{OE}$ to $Y_N$		2.7V	1	5	8.4	1	8.6	1	10.3	ns
			3.3V ± 0.3V	1.5	4.5	7.4	1.5	7.6	1.5	9.4	
			1.8V ± 0.15V	1	5.8	11.6	1	12.1	1	13.6	
$t_{\text{DIS}} \qquad \begin{array}{c} \text{Disable Time} \\ \overline{\text{OE}} \text{ to } Y_{\text{N}} \end{array}$		Figure 1	2.5V ± 0.2V	1	3.7	7.3	1	7.8	1	9.9	ns
	$OE$ to $Y_N$		2.7V	1	3.8	6.6	1	6.8	1	8.6	
			3.3V ± 0.3V	1.5	3.8	6.3	1.5	6.5	1.5	8	
t <sub>sk(0)</sub>	Output Skew Time		3.3V ± 0.3V	—	_	1.0	_	_	_	1.5	ns

# **Operating Characteristics**

T <sub>A</sub> = +25°C					
Symbol	Parameter	<b>Test Conditions</b>	Vcc	Тур	Unit
			1.8V ± 0.15V	9.9	
C <sub>pd</sub>	Power dissipation capacitance per gate	F = 10 MHz Outputs Enabled	2.5V ± 0.2V	10.2	pF
			3.3V ± 0.3V	10.6	

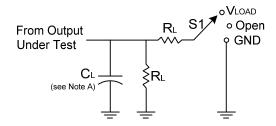
# **Package Characteristics**

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
θ <sub>JA</sub>	Thermal Resistance Junction-to-Ambient	TSSOP-20	(Note 8)	—	74	_	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	TSSOP-20	(Note 8)	_	15	_	°C/W
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	V-QFN4525-20	(Note 8)	_	67	_	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	V-QFN4525-20	(Note 8)	_	20	_	°C/W

Note: 8. Test conditions for TSSOP-20 and V-QFN4525-20: Devices mounted on 4 layer FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout per JESD 51-7.

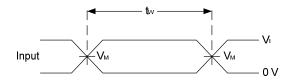


### **Parameter Measurement Information**

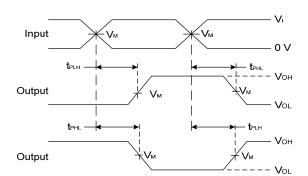


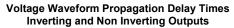
TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	V <sub>LOAD</sub>
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

	In	puts	N.	N/	•	-		
Vcc	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub> V <sub>LOAD</sub>		C∟	RL	VA	
1.8V ± 0.15V	Vcc	≤2ns	V <sub>CC</sub> /2	2 x V <sub>CC</sub>	30pF	1ΚΩ	0.15V	
2.5V ± 0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	$2 \times V_{CC}$	30pF	500Ω	0.15V	
2.7V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V	
3.3V ± 0.3V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V	



#### Voltage Waveform Pulse Duration

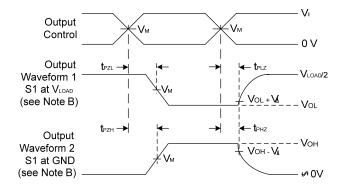




Notes:

- A. Includes test lead and test apparatus capacitance.
- B. All pulses are supplied a pulse repetition rate ≤ 10 MHz.
  C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$
- E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{EN0}$
- F.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD}$ .

Figure 1 Load Circuit and Voltage Waveforms

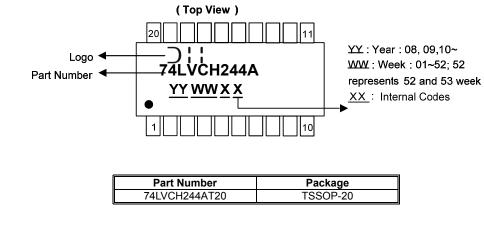


Voltage Waveform Enable and Disable Times Low and High Level Enabling

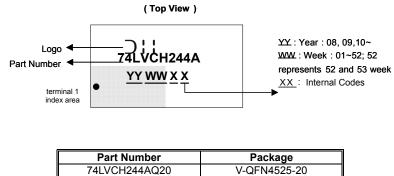


## **Marking Information**

#### (1) TSSOP20



#### QFN-20 (V-QFN4525-20) (2)



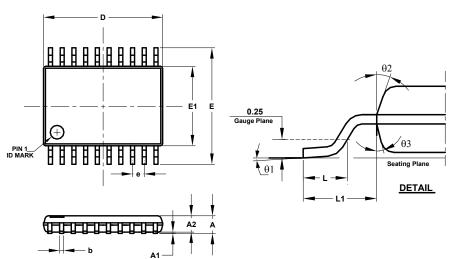
Part Number	Package
74LVCH244AQ20	V-QFN4525-20



## **Package Outline Dimensions**

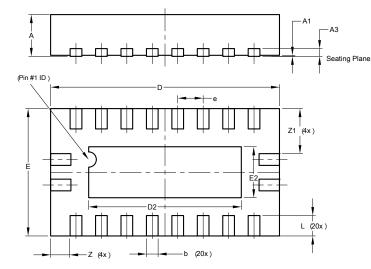
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### (1) TSSOP-20



TSSOP-20					
Dim	Min	Max	Тур		
Α	-	1.20	-		
A1	0.05	0.15	-		
A2	0.80	1.05	-		
b	0.19	0.30	-		
С	0.09	0.20	-		
D	6.40	6.60	6.50		
E	6.20	6.60	6.40		
E1	4.30	4.50	4.40		
е	0.65 BSC				
L	0.45	0.75	0.60		
L1	1.0 REF				
θ1	0°	8°	-		
θ2	10°	14°	12°		
θ3	10°	14°	12°		
All Dimensions in mm					

#### (2) QFN-20 (V-QFN4525-20)



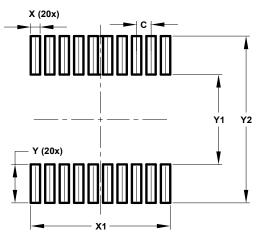
V-QFN4525-20				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05	0.02	
A3	-	-	0.15	
b	0.18	0.30	0.23	
D	4.45	4.55	4.50	
D2	2.85	3.15	3.00	
E	2.45	2.55	2.50	
E2	0.85	1.15	1.00	
е	0.50BSC			
L	0.30	0.50	0.40	
Z	-	-	0.385	
Z1	-	-	0.885	
All Dimensions in mm				



# **Suggested Pad Layout**

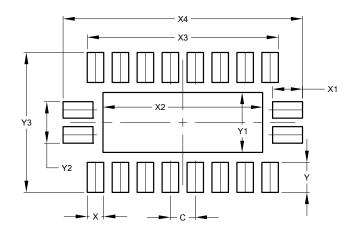
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### (1) TSSOP-20



Dimensions	Value (in mm)	
С	0.650	
Х	0.420	
X1	6.270	
Y	1.789	
Y1	4.160	
Y2	7.720	

#### (2) QFN-20 (V-QFN4525-20)



Dimensions	Value (in mm)	
С	0.500	
Х	0.330	
X1	0.600	
X2	3.200	
X3	3.830	
X4	4.800	
Y	0.600	
Y1	1.200	
Y2	0.830	
Y3	2.800	



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